

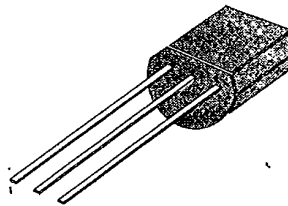
KSC1072**NPN EPITAXIAL SILICON TRANSISTOR****LOW FREQUENCY POWER AMPLIFIER**

- Complement to KSA707
- Collector-Base Voltage $V_{CB0} = 60V$
- Collector Dissipation $P_C = 800mW$

ABSOLUTE MAXIMUM RATINGS ($T_a = 25^\circ C$)

Characteristic	Symbol	Rating	Unit
Collector-Base Voltage	V_{CB0}	60	V
Collector-Emitter Voltage	V_{CE0}	45	V
Emitter-Base Voltage	V_{EB0}	5	V
Collector Current	I_C	700	mA
Collector Dissipation	P_C	800	mW
Junction Temperature	T_j	150	$^\circ C$
Storage Temperature	T_{stg}	-55 ~ 150	$^\circ C$

TO-92



1. Emitter 2. Base 3. Collector

ELECTRICAL CHARACTERISTICS ($T_a = 25^\circ C$)

Characteristic	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector-Base Breakdown Voltage	BV_{CB0}	$I_C = 100\mu A, I_E = 0$	60			V
Collector-Emitter Breakdown Voltage	BV_{CE0}	$I_C = 10mA, I_B = 0$	45			V
Emitter-Base Breakdown Voltage	BV_{EB0}	$I_E = -100\mu A, I_C = 0$	5			V
Collector Cut-off Current	I_{CBO}	$V_{CB} = 40V, I_E = 0$			0.1	μA
Emitter Cut-off Current	I_{EBO}	$V_{EB} = 3V, I_C = 0$			0.1	μA
DC Current Gain	h_{FE}	$V_{CE} = 2V, I_C = 50mA$	40		240	
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C = 0.5A, I_B = 50mA$		0.24	0.4	V
Base-Emitter Saturation Voltage	$V_{BE(sat)}$	$I_C = 0.5A, I_B = 50mA$	0.7	0.89	1.1	V
Output Capacitance	C_{ob}	$V_{CB} = 10V, I_E = 0$ $f = 1MHz$		12		pF

 h_{FE} CLASSIFICATION

Classification	R	O	Y
h_{FE}	40-80	70-140	120-240



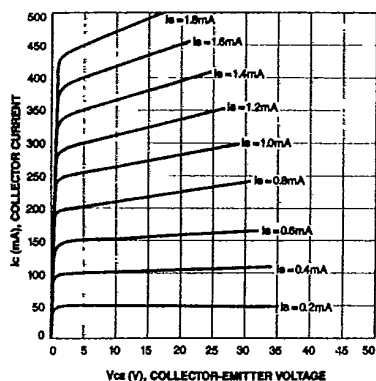
SAMSUNG SEMICONDUCTOR

KSC1072

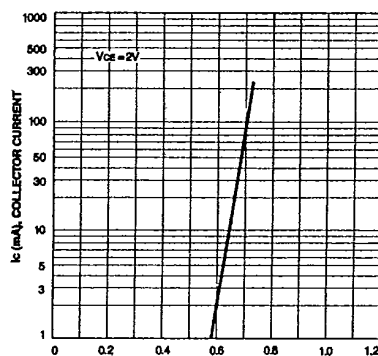
NPN EPITAXIAL SILICON TRANSISTOR

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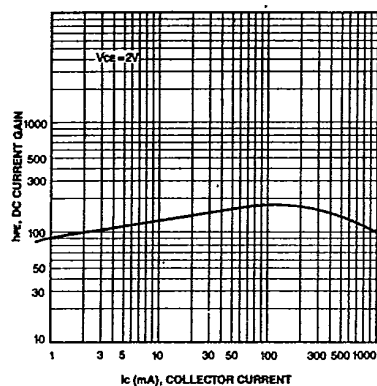
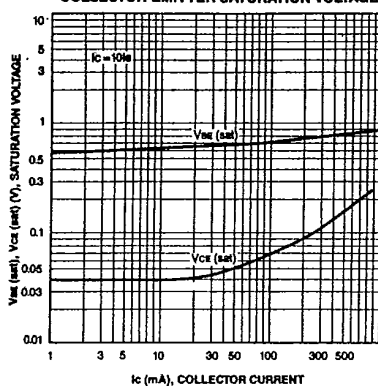
STATIC CHARACTERISTIC



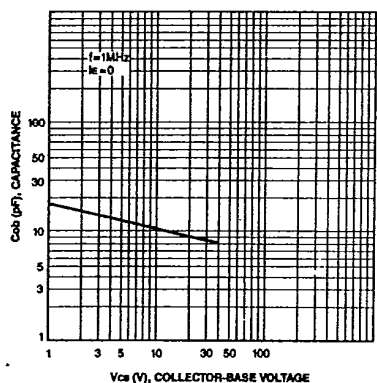
BASE-EMITTER ON VOLTAGE



DC CURRENT GAIN

BASE-EMITTER SATURATION VOLTAGE
COLLECTOR-EMITTER SATURATION VOLTAGE

COLLECTOR OUTPUT CAPACITANCE



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SAMSUNG SEMICONDUCTOR

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